

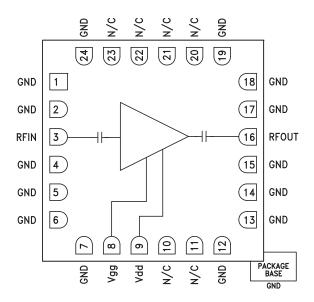


Typical Applications

This HMC772LC4 is ideal for:

- Wideband Communication Systems
- Surveillance Systems
- Point-to-Point Radios
- Point-to-Multi-Point Radios
- Military & Space
- Test Instrumentation

Functional Diagram



HMC772LC4

GaAs HEMT MMIC LOW NOISE AMPLIFIER, 2 - 12 GHz

Features

Noise Figure: 1.8 dB Gain: 15 dB Output IP3: +25 dBm P1dB Output Power: +13 dBm 50 Ohm Matched Input/Output Supply Voltage: +4V @ 45 mA 24 Lead Ceramic 4x4mm SMT Package: 16mm²

General Description

The HMC772LC4 is a GaAs MMIC HEMT Low Noise Wideband Amplifier which operates between 2 and 12 GHz. The amplifier provides 15 dB of gain, 1.8 dB noise figure up to 12 GHz and output IP3 of +25 dBm, while requiring only 45 mA from a +4V supply voltage. The Psat output power of up to +15 dBm enables the LNA to function as a LO driver for many of HIttite's balanced, I/Q or image reject mixers. The HMC772LC4 also features I/Os that are DC blocked and internally matched to 50 Ohms, making it ideal for SMT based high capacity microwave radio applications. The HMC772LC4 is housed in a RoHS compliant 4x4 mm QFN leadless ceramic package.

Electrical Specifications, $T_A = +25^{\circ}$ C, Vdd= +4V, Idd = 45 mA*

Parameter	Min.	Тур.	Max.	Units
Frequency Range		2 - 12		
Gain	14	15		dB
Gain Variation over Temperature		0.01		dB / °C
Noise Figure		1.8	2.5	dB
Input Return Loss		15		dB
Output Return Loss		15		dB
Output Power for 1 dB Compression		13		dBm
Output Third Order Intercept (IP3)		25		dBm
Supply Current (Idd) (Vdd = 4V, Vgg = -0.2V Typ.)*		45		mA

* Adjust Vgg between -1 to 0.3V to achieve Idd = 45mA typical.

For price, delivery and to place orders: Hittite Microwave Corporation, 20 Alpha Road, Chelmsford, MA 01824 Phone: 978-250-3343 Fax: 978-250-3373 Order On-line at www.hittite.com Application Support: Phone: 978-250-3343 or apps@hittite.com



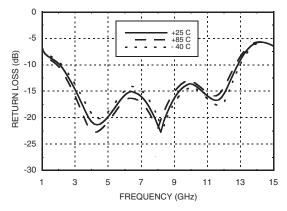


HMC772LC4

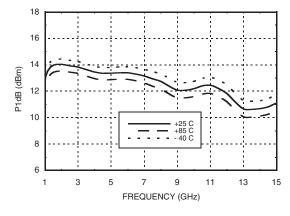
GaAs HEMT MMIC LOW NOISE AMPLIFIER, 2 - 12 GHz

Gain vs. Temperature 20 +25 C +85 C - 40 C 18 GAIN (dB) 16 14 12 10 13 3 5 11 15 7 9 1 FREQUENCY (GHz)

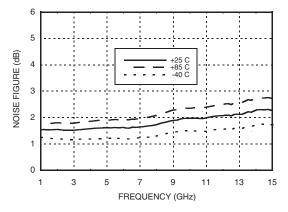
Output Return Loss vs. Temperature



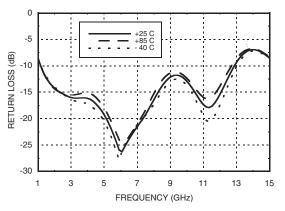
Output P1dB vs. Temperature



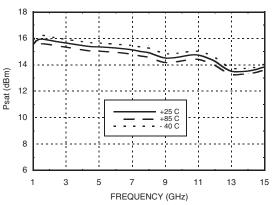




Input Return Loss vs. Temperature



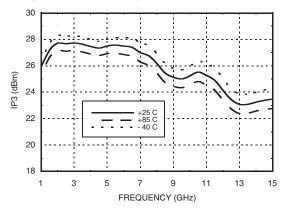
Output Psat vs. Temperature



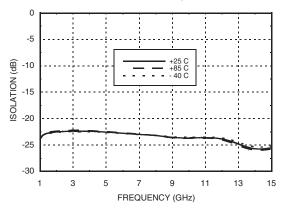




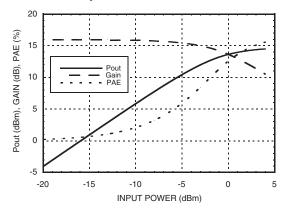
Output IP3 vs. Temperature



Reverse Isolation vs. Temperature



Power Compression @ 12 GHz

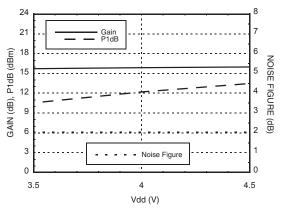


GaAs HEMT MMIC LOW NOISE

AMPLIFIER, 2 - 12 GHz

HMC772LC4

Gain, Noise Figure & Power vs. Supply Voltage @ 12 GHz





HMC772LC4

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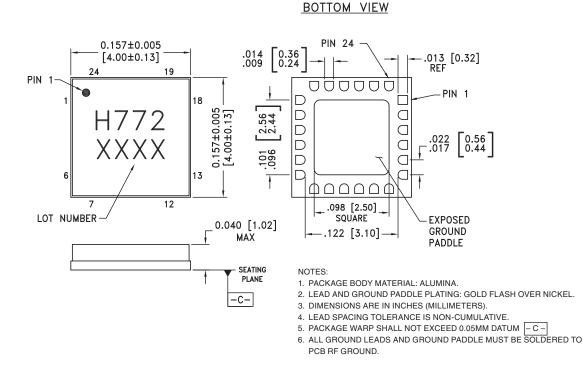


Absolute Maximum Ratings

Drain Bias Voltage	+5V	
Drain Bias Current	60 mA	
RF Input Power	5 dBm	
Gate Bias Voltage	-1 to 0.3 V	
Continuous Pdiss (T = 85 °C) (derate 5.8 mW/°C above 85 °C)	0.55 W	
Thermal Resistance (Channel to ground paddle)	172 °C/W	
Channel Temperature	180 °C	
Storage Temperature	-65 to +150 °C	
Operating Temperature	-40 to +85 °C	



Outline Drawing



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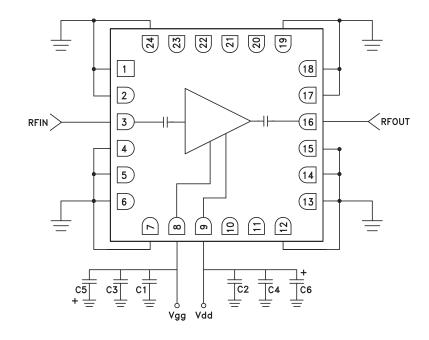
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ROHS V EARTH FRIENDLY

Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1, 2, 4 - 7, 12 - 15, 17 - 19, 24	GND	These pins and ground paddle must be connected to RF/DC ground.	
3	RFIN	This pin is AC coupled and matched to 50 Ohms.	
8	Vgg	Gate control for amplifier. Please follow "MMIC Amplifier Biasing Procedure" application note. See application circuit for required external components.	Vgg 0
9	Vdd	Power Supply Voltage for the amplifier. See application circuit for required external components.	Vdd O
10, 11, 20 - 23	N/C	The pins are not connected internally; however, all data shown herein was measured with these pins connected to RF/DC ground externally.	
16	RFOUT	This pin is AC coupled — RFOUT	

Application Circuit



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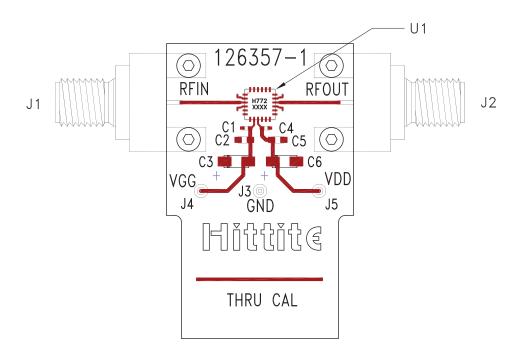


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Evaluation PCB



List of Materials for Evaluation PCB 126359^[1]

Item	Description
J1, J2	PCB Mount 2.92mm K-Connector
J3 - J5	DC Pin
C1, C4	100 pF Capacitor, 0402 Pkg.
C2, C5	1000 pF Capacitor, 0603 Pkg.
C3, C6	4.7 µF Capacitor, Tantalum
U1	HMC772LC4 Amplifier
PCB [2]	126357 Evaluation PCB

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350 or Arlon 25FR

The circuit board used in this application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.